

Silicon Carbide MOSFET 1200V, 50m Ω

General Description

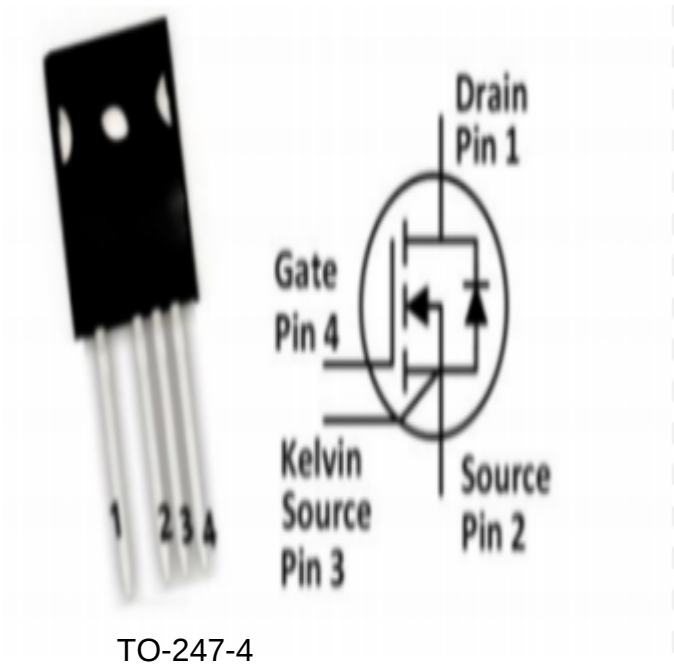
This product family offers state of the art performance. It is designed for high frequency applications here high efficiency and high reliability are required.

Features

- High voltage, low on resistance
- High speed, low parasitic capacitance
- High junction temperature
- Fast recovery diode
- Kelvin connection driver

Applications

- motor drive
- Photovoltaic inverter
- UPS power supply
- High voltage DC / DC converter
- Switching Mode Power Supply



Key performance parameters

Type	V_{DS}	I_D $T_C=25^{\circ}C$	$R_{DS(ON)}$
KN3M0050120Q	1200V	58A	50m Ω

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Maximum Ratings $T_C=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-source voltage $V_{GS} = 0\text{V}$, $I_D = 100\ \mu\text{A}$	V_{DS}	1200	V
Gate-source voltage Recommended maximum	V_{GS}	-5 to 20	V

Maximum Ratings $T_C=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current : $V_{GS} = 20\text{V}$ $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_D	58 43	A
Pulsed drain current: Pulse width limited by SOA	I_{DM}	145	A
Power dissipation : $T_C = 25^{\circ}\text{C}$	P_{TOT}	344	W
Storage temperature range :	T_{stg}	-55 to +175	$^{\circ}\text{C}$
Operating and junction temperature:	T_j	-55 to +175	$^{\circ}\text{C}$
Soldre temperature: Wave soldering only allowed at leads, 1.6 mm from case for 10 s	T_L	260	$^{\circ}\text{C}$

Thermal Resistance

Parameter	Symbol	Typ.	Unit
Thermal resistance to shell	R_{thJC}	0.436	$^{\circ}\text{C}/\text{W}$

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Electrical Characteristic

 $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Zero gate voltage drain current	I _{DSS}		5	100	μA	V _{DS} = 1200V V _{GS} = 0V
Gate leakage current	I _{GSS}		1	±100	nA	V _{DS} = 0V V _{GS} = -5~20V
Gate threshold voltage	V _{TH}		3.2 2.2		V	V _{GS} = V _{DS} I _D = 6mA T _C =175° C
Drain-source on-state resistance	R _{ON}		50 80	65	m Ω	V _{GS} = 20V I _D = 20A T _J = 25℃ T _J = 175℃
Input capacitance	C _{iss}		2750		pF	V _{DS} = 800V V _{GS} = 0V f = 1MHz V _{AC} = 25mV
Output capacitance	C _{oss}		106			
Reverse transfer capacitance	C _{rss}		5.2			
The output capacitor stores energy	E _{oss}		43		μ J	
Total gate charge	Q _g		120		nC	V _{DS} = 800V I _D = 20A V _{GS} = -5 to 20V
Gate to source charge	Q _{gs}		25			
Gate to drain charge	Q _{gd}		48			
Gate input resistance	R _g		2.8		Ω	f=1MHz
Tuen-on switching energy	E _{ON}		455.4		μ J	V _{DS} = 800V, I _D = 30A, V _{GS} = -2 to 20V, R _{G(ext)} =3.3 Ω , L = 450 μ H
Turn-off switching energy	E _{OFF}		213.6		μ J	
Turn-on delay time	t _{d(on)}		8.9		ns	
Rise time	t _r		28.9			

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Turn-off delay time	$t_{d(off)}$		25.6			
Fall time	t_f		17.2			

Reverse Diode Characteristics

$T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}		4.9 4.4		V	$I_{SD} = 20\text{A}$ $V_{GS} = 0\text{V}$ $T_J = 175^\circ\text{C}$
Reverse recovery time	t_{rr}		44.4		ns	$V_{GS} = -2\text{V}/+20\text{V}$, $I_{SD} = 30\text{A}$, $V_R = 800\text{V}$, $di/dt = 1000\text{A}/\mu\text{s}$, $R_{G(ext)} = 10\ \Omega$ $L = 450\ \mu\text{H}$
Reverse recovery charge	Q_{rr}		212.6		nC	
Reverse recovery peak current	I_{RRM}		10.8		A	

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Characteristics Curves

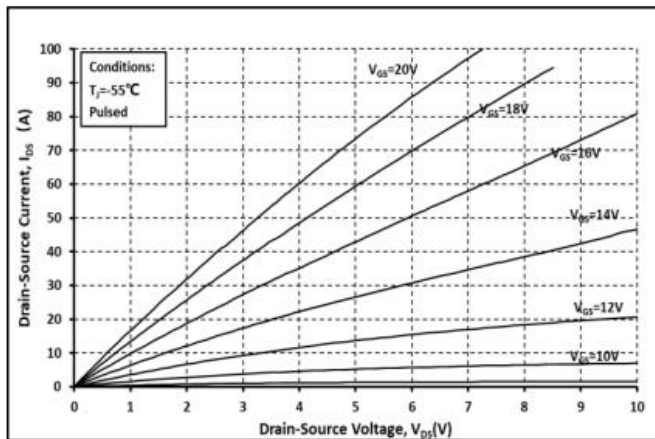


图. 1 输出曲线 @ $T_j = -55^\circ\text{C}$

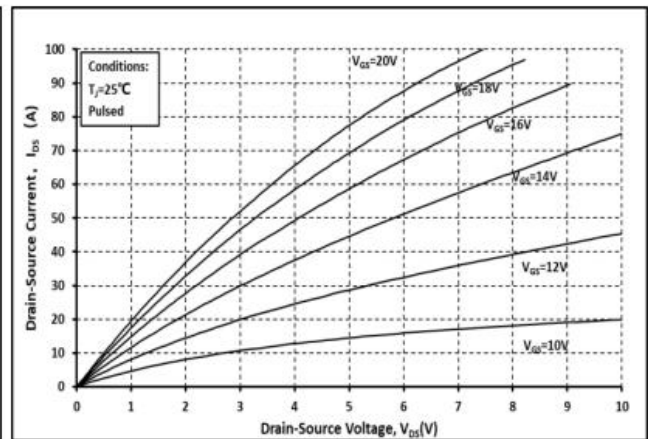


图. 2 输出曲线 @ $T_j = 25^\circ\text{C}$

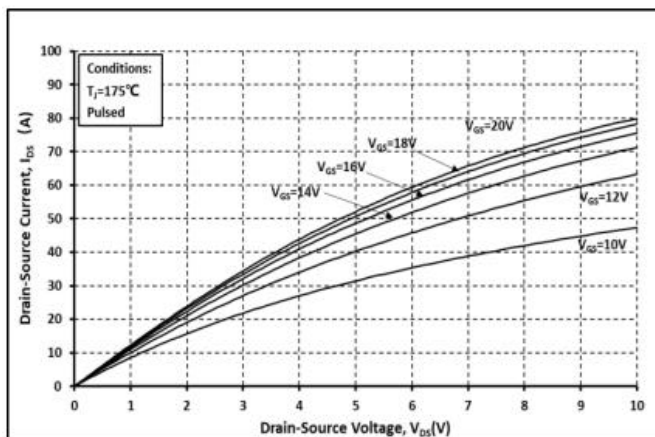


图. 3 输出曲线 @ $T_j = 175^\circ\text{C}$

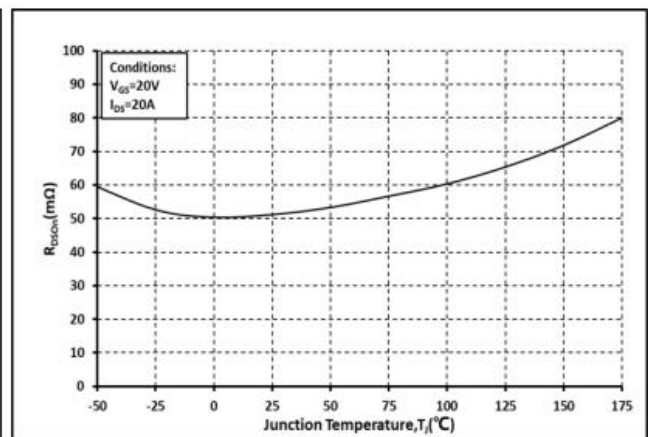


图. 4 R_{on} 和温度关系曲线

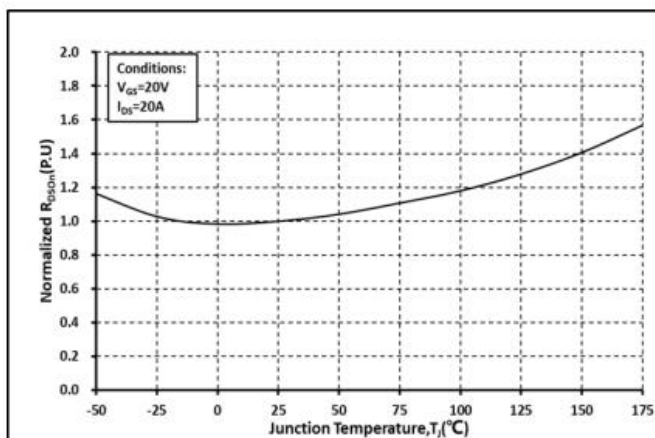


图. 5 归一化的 R_{on} 和温度关系曲线

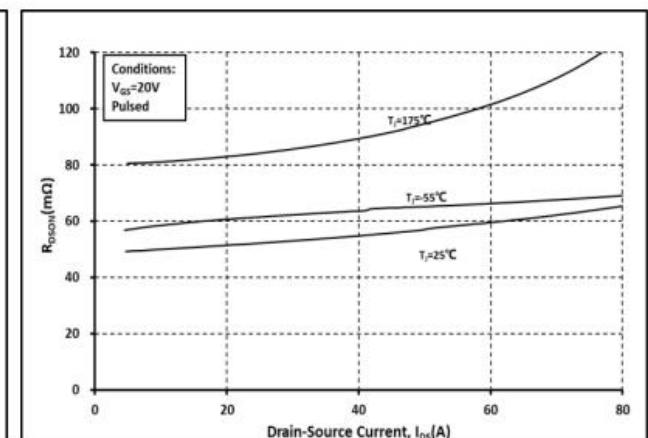


图. 6 各温度下的 R_{on} 和 I_{DS} 关系曲线

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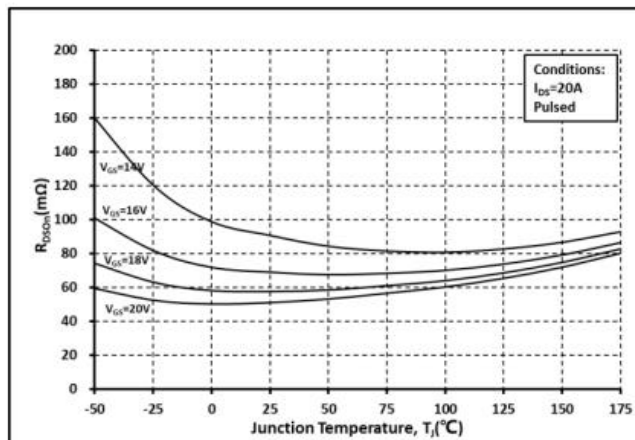
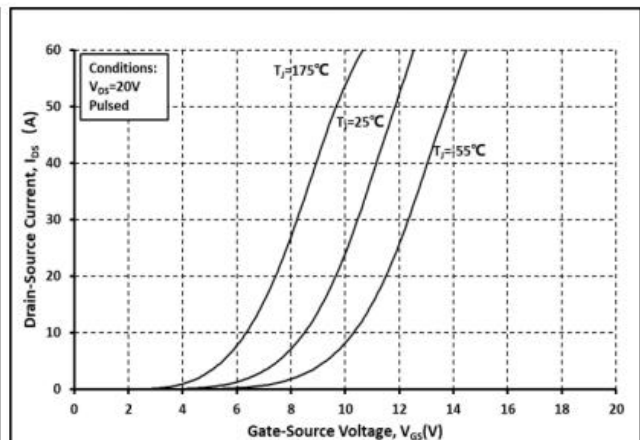
图. 7 各 V_{GS} 下的 R_{on} 和温度关系曲线

图. 8 各温度下的传输特性曲线

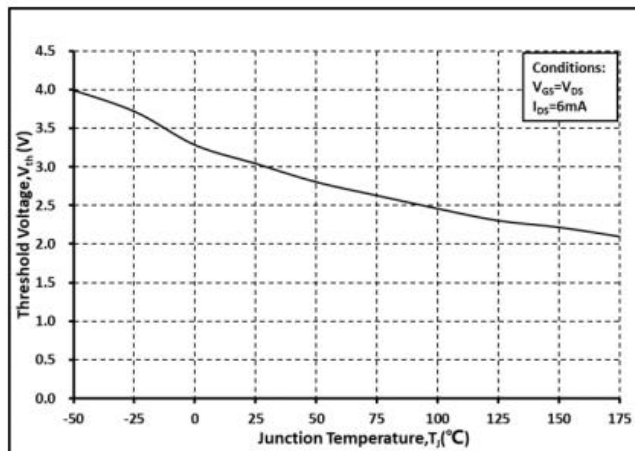
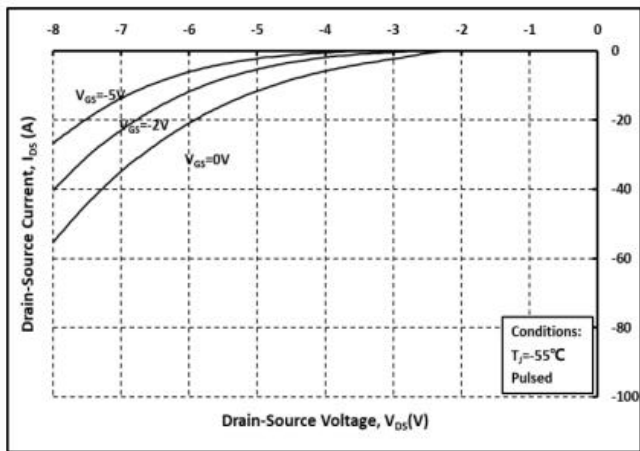
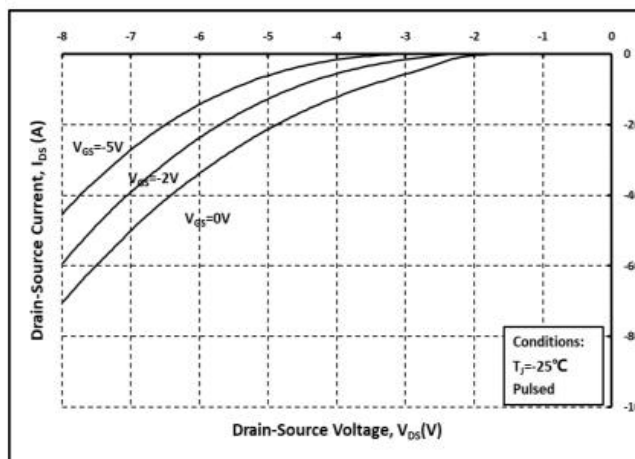
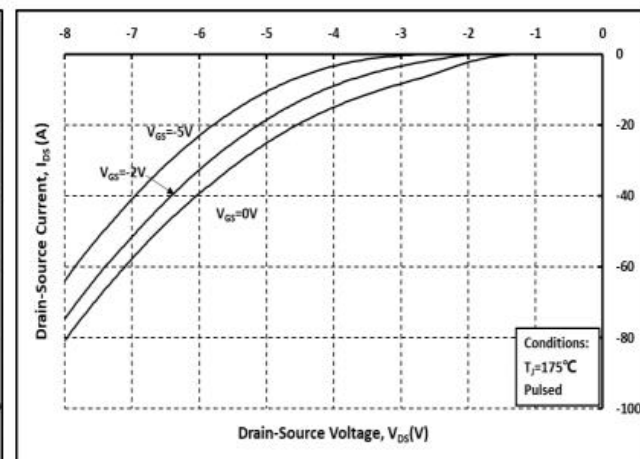


图. 9 阈值电压随温度变化曲线

图. 10 体二极管导通曲线 @ $T_j = -55°C$ 图. 11 体二极管导通曲线 @ $T_j = 25°C$ 图. 12 体二极管导通曲线 @ $T_j = 175°C$

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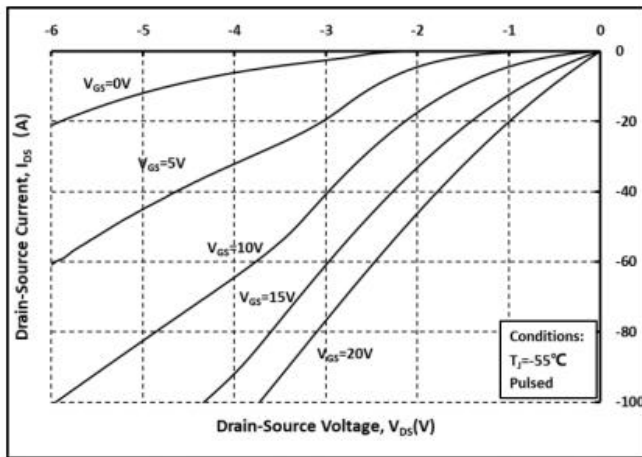
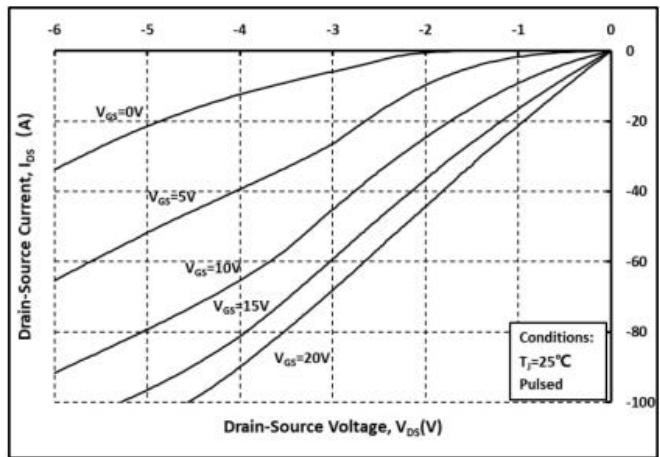
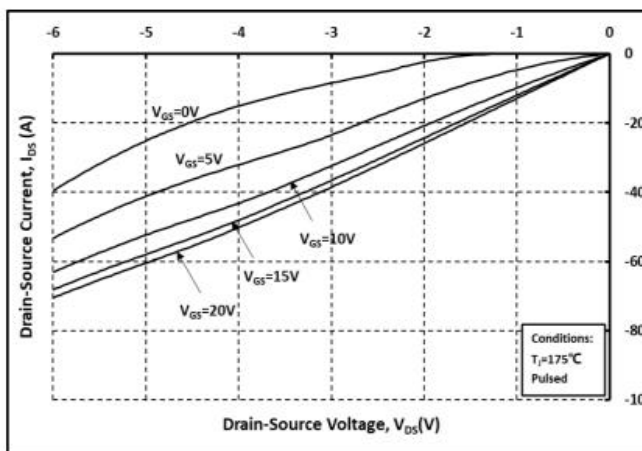
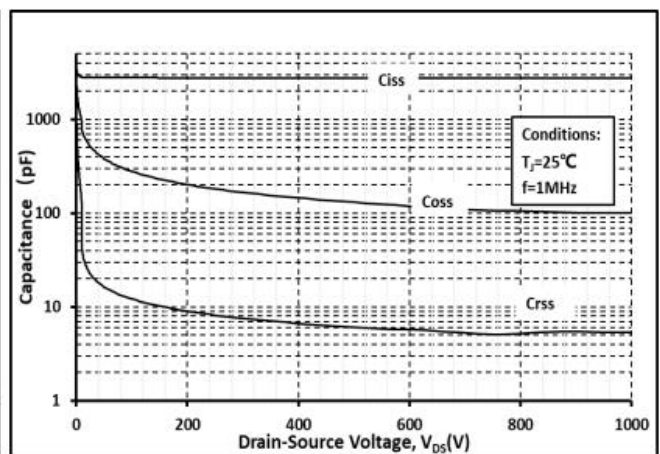
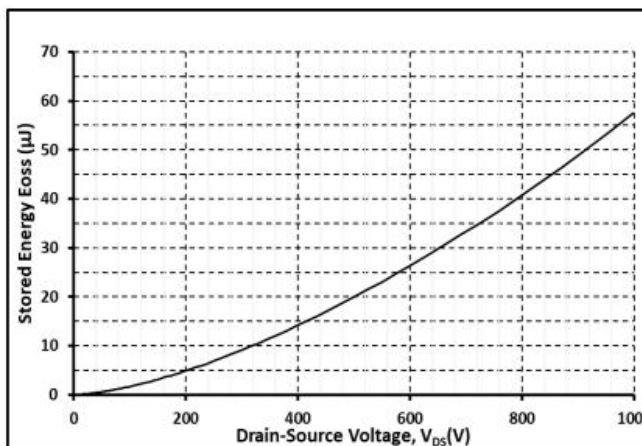
图. 13 第三象限曲线 @ $T_j = -55^\circ\text{C}$ 图. 14 第三象限曲线 @ $T_j = 25^\circ\text{C}$ 图. 15 第三象限曲线 @ $T_j = 175^\circ\text{C}$ 图. 16 各电容和 V_{ds} 关系曲线

图. 17 输出电容存储能量曲线

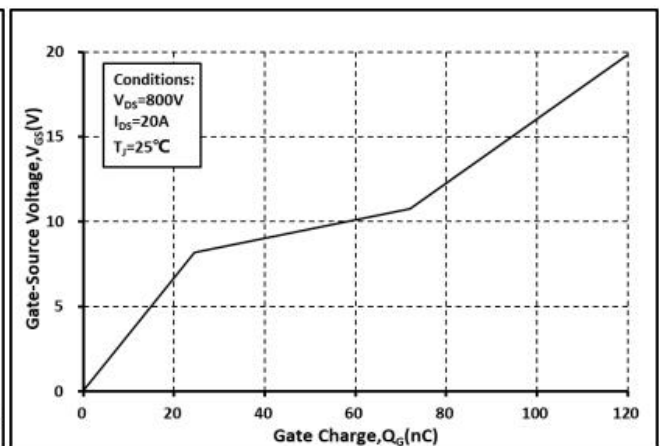


图. 18 栅电荷特征曲线

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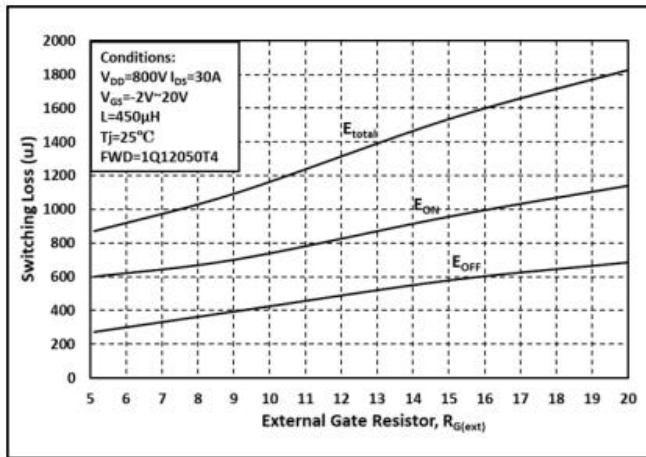


图. 19 开关能量和栅极电阻 $R_{G(ext)}$ 关系曲线

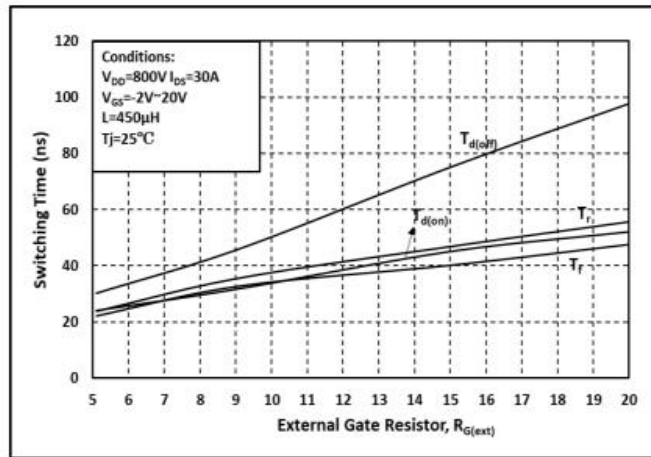


图. 20 开关时间和栅极电阻 $R_{G(ext)}$ 关系曲线

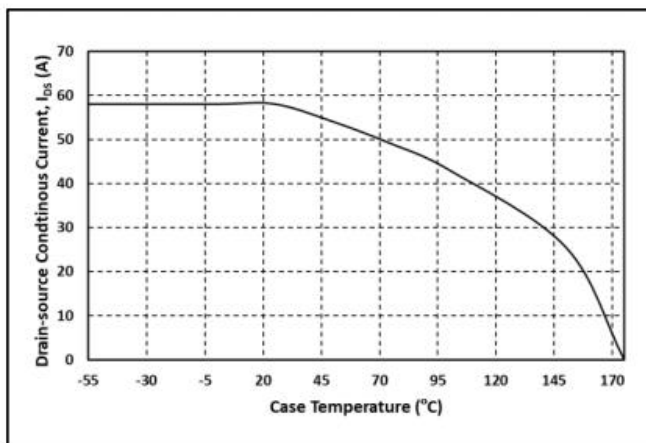


图. 21 漏端电流和温度关系曲线

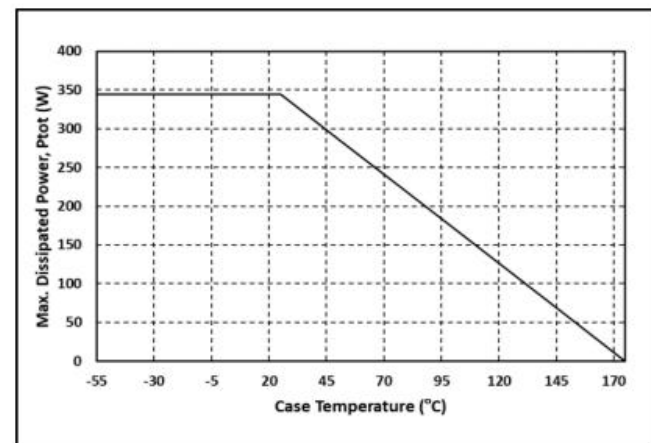


图. 22 最大功耗降额和温度关系曲线

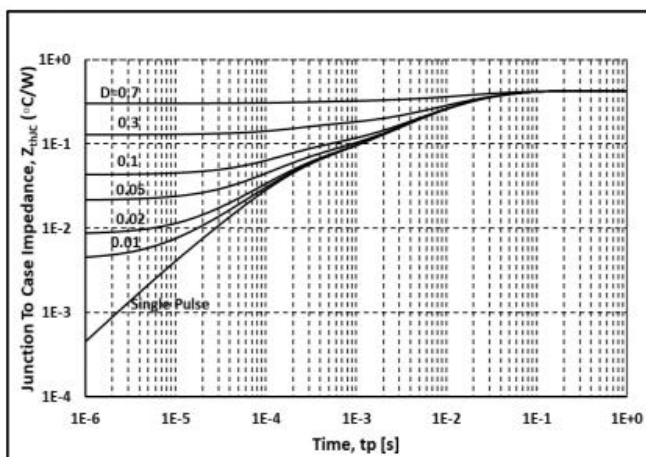


图. 23 热阻曲线

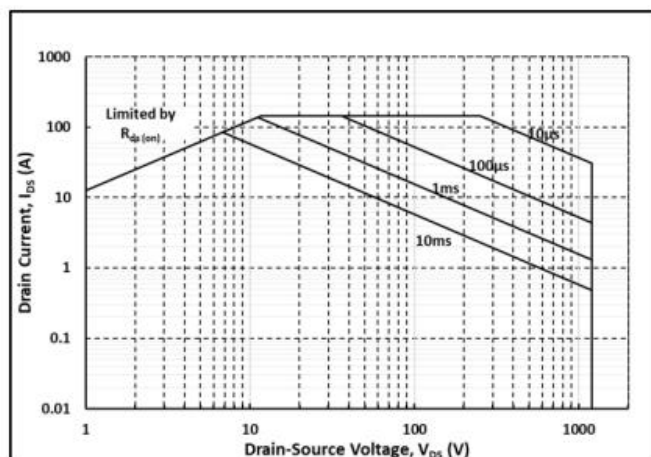
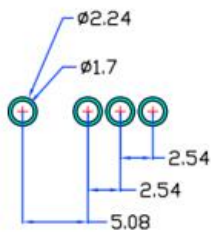
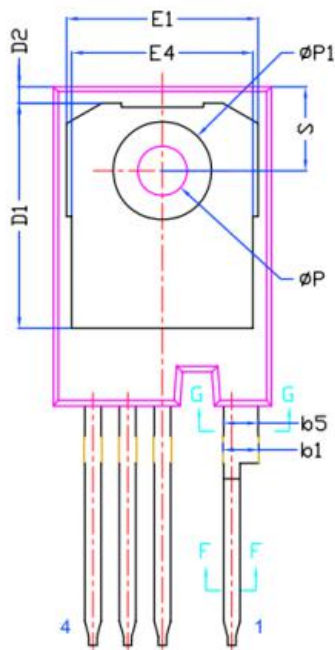
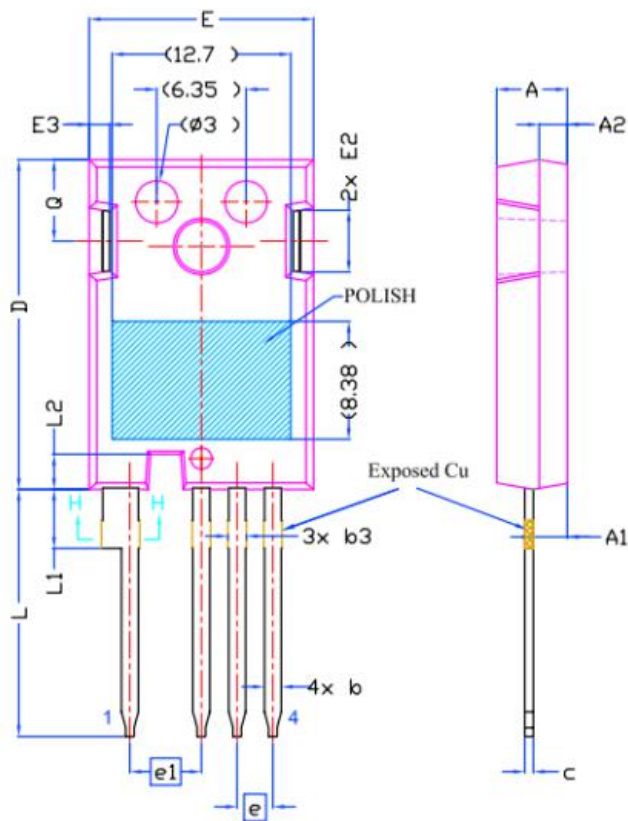


图. 24 安全工作区示意图

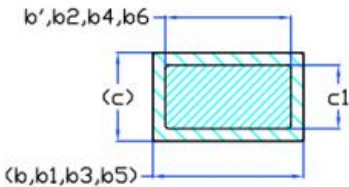
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Package Outline:TO-247-4



Recommended Solder Pad Layout

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.83	5.02	5.21
A1	2.29	2.41	2.54
A2	1.91	2.00	2.16
b'	1.07	1.20	1.28
b	1.07	1.20	1.33
b1	2.39	2.67	2.94
b2	2.39	2.67	2.84
b3	1.07	1.30	1.60
b4	1.07	1.30	1.50
b5	2.39	2.53	2.69
b6	2.39	2.53	2.64
c	0.55	0.60	0.68
c1	0.55	0.60	0.65
D	23.30	23.45	23.60
D1	16.25	16.55	17.65
D2	0.95	1.19	1.25
E	15.75	15.94	16.13
E1	13.10	14.02	14.15
E2	3.68	4.40	5.10
E3	1.00	1.45	1.90
E4	12.38	13.26	13.43
e	2.54 BSC		
e1	5.08 BSC		
L	17.31	17.57	17.82
L1	3.97	4.19	4.37
L2	2.35	2.50	2.65
ØP	3.51	3.61	3.65
ØP1	7.19 REF.		
Q	5.49	5.79	6.00
S	6.04	6.17	6.30



Section F--F, G--G, H--H

说明:

- 1. 封装标准参考: : JEDEC TO247, Variation AD
- 2. 以上单位为: 毫米
- 3. 需要开槽, 槽口可为圆形
- 4. 尺寸 D 和 E 不包括模具溢料

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